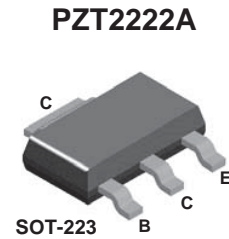
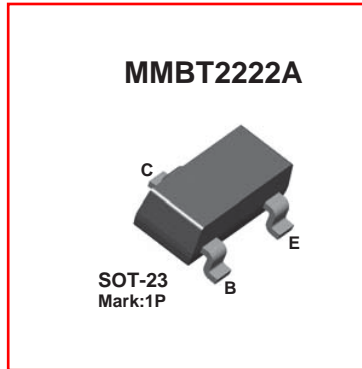


PN2222A / MMBT2222A / PZT2222A NPN General Purpose Amplifier

Features

- This device is for use as a medium power amplifier and switch requiring collector currents up to 500mA.
- Sourced from process 19.



Absolute Maximum Ratings * $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	75	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current	1.0	A
T_{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These rating are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.			Units
		PN2222A	*MMBT2222A	**PZT2222A	
P_D	Total Device Dissipation Derate above 25°C	625	350	1,000	mW
		5.0	2.8	8.0	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	$^\circ\text{C}/\text{W}$

* Device mounted on FR-4 PCB $1.6'' \times 1.6'' \times 0.06''$.

** Device mounted on FR-4 PCB $36\text{mm} \times 18\text{mm} \times 1.5\text{mm}$; mounting pad for the collector lead min. 6cm^2 .

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
$BV_{(BR)CEO}$	Collector-Emitter Breakdown Voltage *	$I_C = 10\text{mA}, I_B = 0$	40		V
$BV_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	75		V
$BV_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
I_{CEX}	Collector Cutoff Current	$V_{CE} = 60\text{V}, V_{EB(off)} = 3.0\text{V}$		10	nA
I_{CBO}	Collector Cutoff Current	$V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 60\text{V}, I_E = 0, T_a = 125^\circ\text{C}$		0.01 10	μA μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0\text{V}, I_C = 0$		10	nA
I_{BL}	Base Cutoff Current	$V_{CE} = 60\text{V}, V_{EB(off)} = 3.0\text{V}$		20	nA
On Characteristics					
h_{FE}	DC Current Gain	$I_C = 0.1\text{mA}, V_{CE} = 10\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}, T_a = -55^\circ\text{C}$ $I_C = 150\text{mA}, V_{CE} = 10\text{V}^*$ $I_C = 150\text{mA}, V_{CE} = 1\text{V}^*$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}^*$	35 50 75 35 100 50 40	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage *	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$		0.3 1.0	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage *	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$	0.6	1.2 2.0	V V
Small Signal Characteristics					
f_T	Current Gain Bandwidth Product	$I_C = 20\text{mA}, V_{CE} = 20\text{V}, f = 100\text{MHz}$	300		MHz
C_{obo}	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		8.0	pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5\text{V}, I_C = 0, f = 1\text{MHz}$		25	pF
$rb'C_c$	Collector Base Time Constant	$I_C = 20\text{mA}, V_{CB} = 20\text{V}, f = 31.8\text{MHz}$		150	pS
NF	Noise Figure	$I_C = 100\mu\text{A}, V_{CE} = 10\text{V},$ $R_S = 1.0\text{K}\Omega, f = 1.0\text{KHz}$		4.0	dB
$Re(h_{ie})$	Real Part of Common-Emitter High Frequency Input Impedance	$I_C = 20\text{mA}, V_{CE} = 20\text{V}, f = 300\text{MHz}$		60	Ω
Switching Characteristics					
t_d	Delay Time	$V_{CC} = 30\text{V}, V_{EB(off)} = 0.5\text{V},$ $I_C = 150\text{mA}, I_{B1} = 15\text{mA}$		10	ns
t_r	Rise Time			25	ns
t_s	Storage Time	$V_{CC} = 30\text{V}, I_C = 150\text{mA},$ $I_{B1} = I_{B2} = 15\text{mA}$		225	ns
t_f	Fall Time			60	ns

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Performance Characteristics

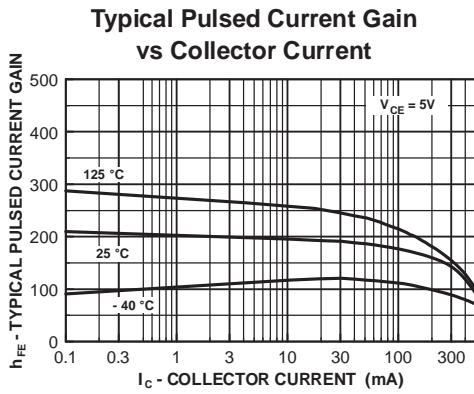


Figure 1. Typical Pulsed Current Gain vs Collector Current

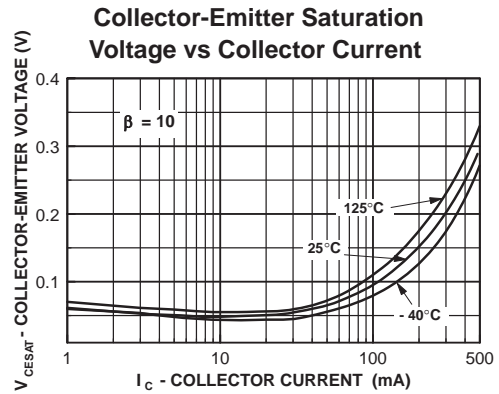


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

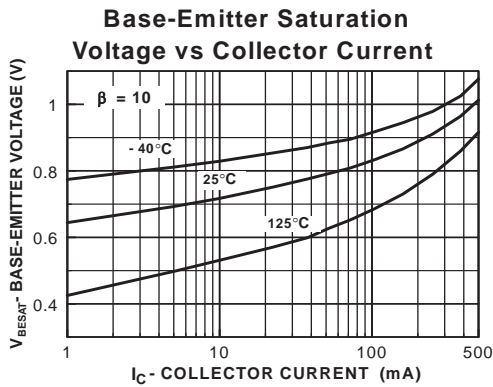


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

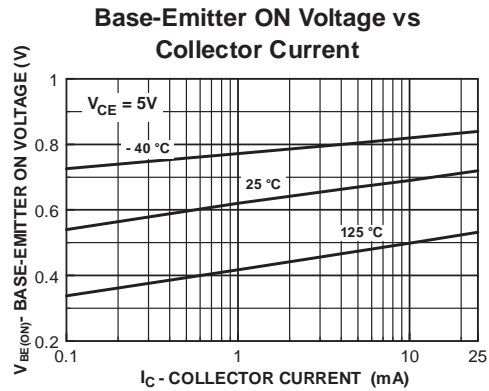


Figure 4. Base-Emitter On Voltage vs Collector Current

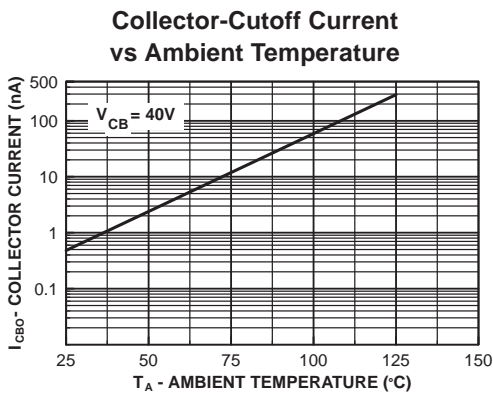


Figure 5. Collector Cutoff Current vs Ambient Temperature

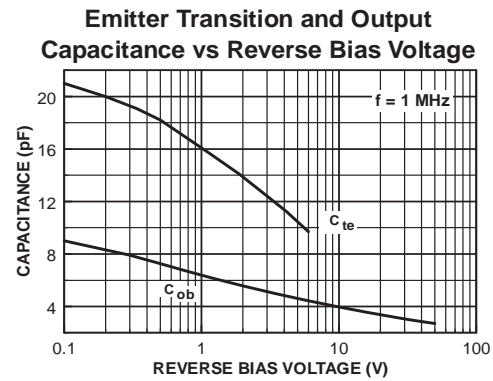


Figure 6. Emitter Transition and Output Capacitance vs Reverse Bias Voltage

Typical Performance Characteristics

(Continued)

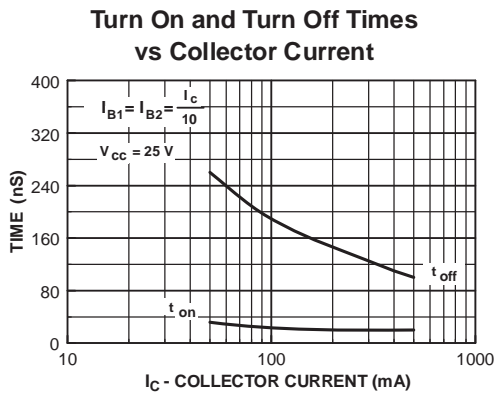


Figure 7. Turn On and Turn Off Times vs Collector Current

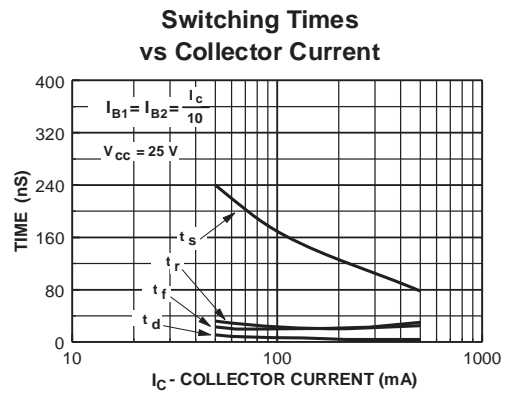


Figure 8. Switching Times vs Collector Current

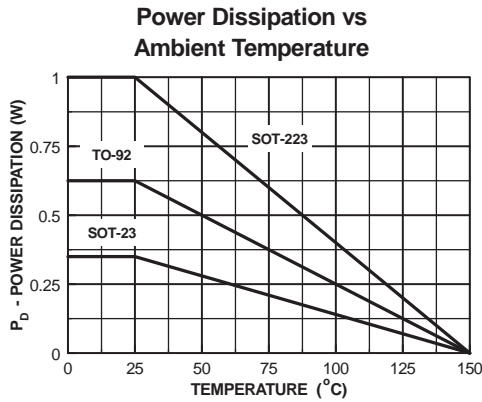


Figure 9. Power Dissipation vs Ambient Temperature

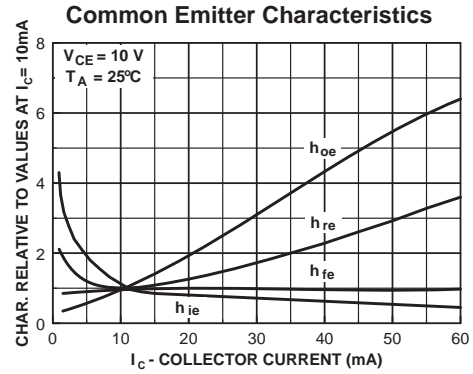


Figure 10. Common Emitter Characteristics

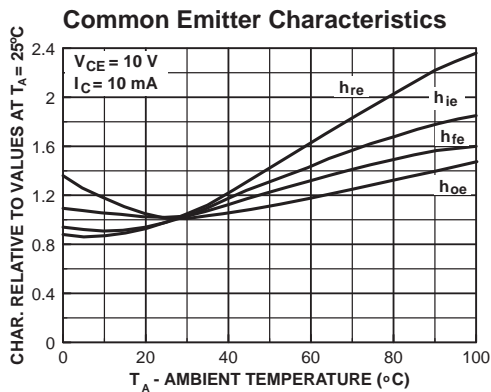


Figure 11. Common Emitter Characteristics

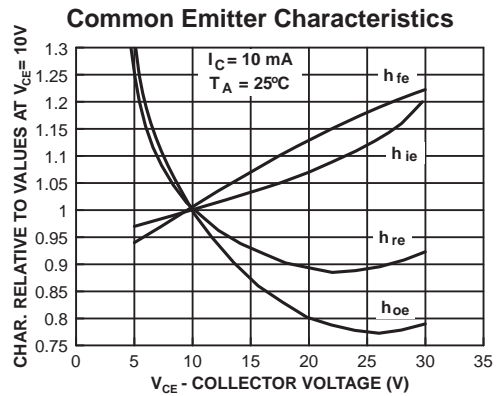


Figure 12. Common Emitter Characteristics



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|--------------------------|-------------------------------------|---------------------------------------|---|
| AccuPower™ | F-PFS™ | Power-SPM™ | <p>SYSTEM GENERAL
The Power Franchise®
the power franchise
TinyBoost™
TinyBuck™
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TriFault Detect™
TRUECURRENT™
μSerDes™
 SerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
XST™</p> |
| Auto-SPM™ | FRFET® | PowerTrench® | |
| Build it Now™ | Global Power Resource SM | PowerXS™ | |
| CorePLUS™ | Green FPS™ | Programmable Active Droop™ | |
| CorePOWER™ | Green FPS™ e-Series™ | QFET® | |
| CROSSVOLT™ | Gmax™ | QS™ | |
| CTL™ | GTO™ | Quiet Series™ | |
| Current Transfer Logic™ | IntelliMAX™ | RapidConfigure™ | |
| DEUXPEED® | ISOPLANAR™ | ™ | |
| Dual Cool™ | MegaBuck™ | Saving our world, 1mW/W/kW at a time™ | |
| EcoSPARK® | MICROCOUPLER™ | SignalWise™ | |
| EfficientMax™ | MicroFET™ | SmartMax™ | |
| ESBC™ | MicroPak™ | SMART START™ | |
| ™ | MicroPak2™ | SPM® | |
| Fairchild® | MillerDrive™ | STEALTH™ | |
| Fairchild Semiconductor® | MotionMax™ | SuperFET™ | |
| FACT Quiet Series™ | Motion-SPM™ | SuperSOT™-3 | |
| FACT® | OptoHiT™ | SuperSOT™-6 | |
| FAST® | OPTOLOGIC® | SuperSOT™-8 | |
| FastvCore™ | OPTOPLANAR® | SupreMOS® | |
| FETBench™ | ™ | SyncFET™ | |
| FlashWriter®* | PDP SPM™ | Sync-Lock™ | |
| FPS™ | | | |

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

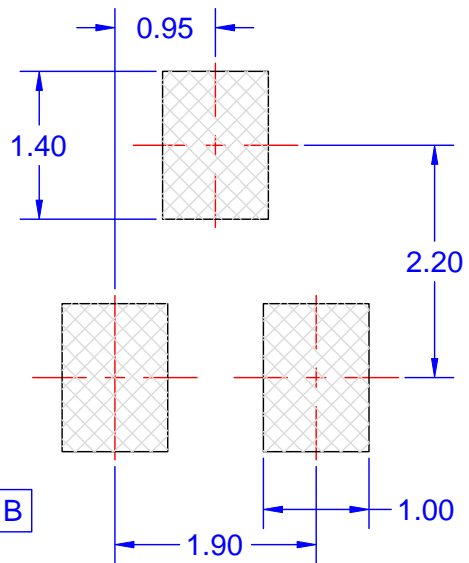
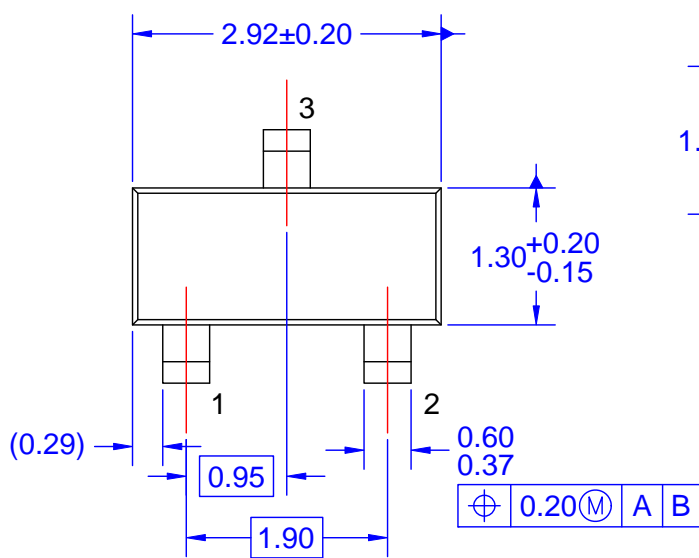
Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

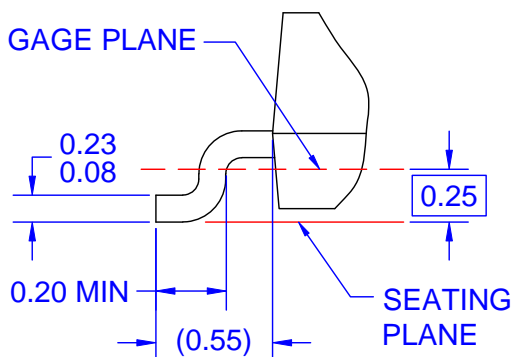
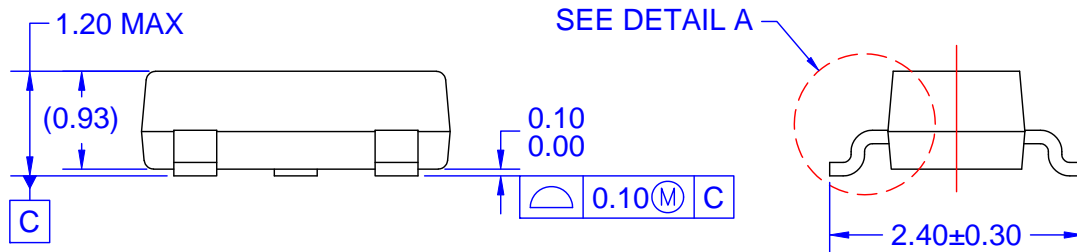
PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.



LAND PATTERN RECOMMENDATION



DETAIL A
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994.
- E) DRAWING FILE NAME: MA03DREV10